

IRFP460A

20A, 500V, 0.22 Ohm, N-Channel SMPS Power MOSFET

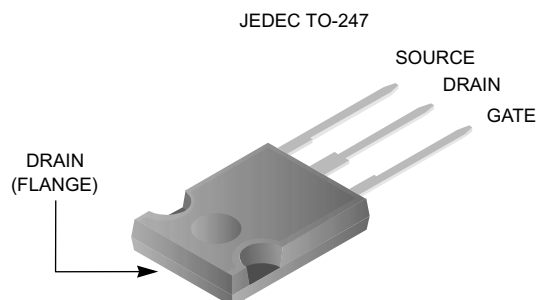
Applications

- Switch Mode Power Supplies (SMPS)
- Uninterruptable Power Supply
- High Speed Power Switching

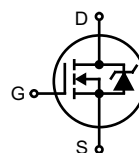
Features

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Improved $r_{DS(ON)}$
- Reduced Miller Capacitance

Package



Symbol



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	500	V
V_{GS}	Gate to Source Voltage	± 30	V
I_D	Drain Current		
	Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$)	20	A
	Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = 10\text{V}$)	13	A
	Pulsed ¹	80	A
P_D	Power dissipation	280	W
	Derate above 25°C	2.2	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	$^\circ\text{C}$
	Soldering Temperature for 10 seconds	300 (1.6mm from case)	$^\circ\text{C}$
	Mounting Torque, 8-32 or M3 Screw	10lbf*in (1.1N*m)	

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	0.45	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance Case to Sink, Flat, Greased Surface	0.24 TYP	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
IRFP460A	IRFP460A	TO-247	-	-	-

Electrical Characteristics $T_J = 25^\circ\text{C}$ (unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	500	-	-	V
$\Delta B_{VDSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	$V_I^\circ\text{C}$ Reference to 25°C , $I_D = 1\text{mA}$	-	0.61	-	
$r_{DS(ON)}$	Drin to Source On-Resistance	$V_{GS} = 10\text{V}$, $I_D = 12\text{A}$	-	0.17	0.22	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.0	3.3	4.0	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 25\text{V}$, $T_C = 25^\circ\text{C}$	-	-	25	μA
		$V_{GS} = 0\text{V}$, $T_C = 150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

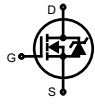
Dynamics

g_{fs}	Forward Transconductance	$V_{DS} = 50\text{V}$, $I_D = 12\text{A}$	11	-	-	S
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 10\text{V}$,	-	56	70	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 400\text{V}$,	-	13	18	nC
Q_{gd}	Gate to Drain "Miller" Charge	$I_D = 20\text{A}$	-	17	22	nC
$t_{d(ON)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}$,	-	13	-	ns
t_r	Rise Time	$I_D = 20\text{A}$	-	8	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time	$R_G = 4.3\Omega$,	-	41	-	ns
t_f	Fall Time	$R_D = 13\Omega$	-	6	-	ns
C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$,	-	3520	-	pF
C_{OSS}	Output Capacitance	$f = 1\text{MHz}$	-	410	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	21	-	pF

Avalanche Characteristics

E_{AS}	Single Pulse Avalanche Energy ²		960	-	-	mJ
I_{AR}	Avalanche Current		-	-	20	A
E_{AR}	Repetitive Avalanche Energy ¹		28	-	-	mJ

Drain-Source Diode Characteristics

I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode. 	-	-	20	A
I_{SM}	Pulsed Source Current ¹ (Body Diode)		-	-	80	A
V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 20\text{A}$	-	0.86	1.8	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 20\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	560	710	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 20\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	8.0	11	μC

Notes:

- 1: Repetitive rating; pulse width limited by maximum junction temperature
2: $V_{DD} = 50\text{V}$, Starting $T_J = 25^\circ\text{C}$, $L = 7.0\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 14\text{A}$
3: $I_{SD} \leq 14\text{A}$, $di/dt \leq 130\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
4: Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$

Typical Characteristics

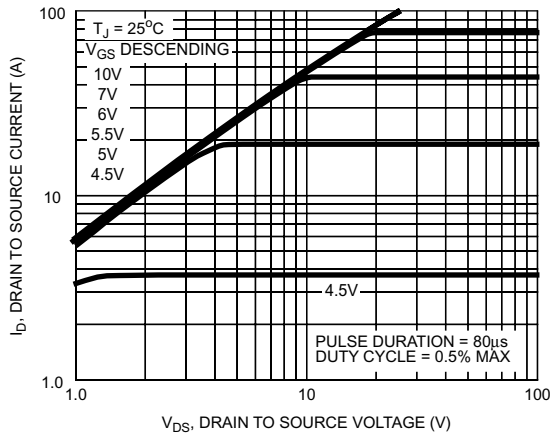


Figure 1. Output Characteristics

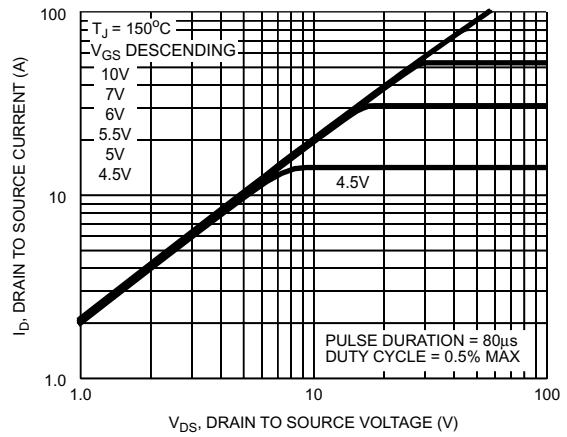


Figure 2. Output Characteristics

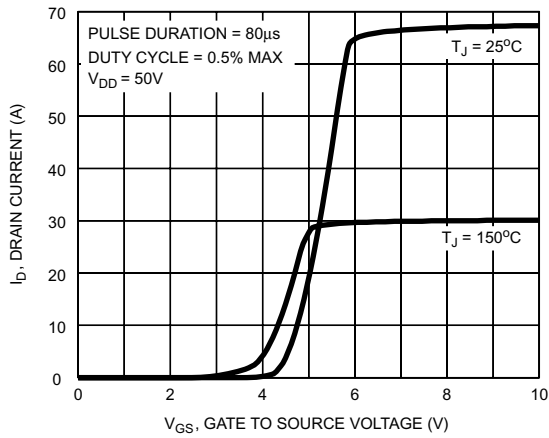


Figure 3. Transfer Characteristics

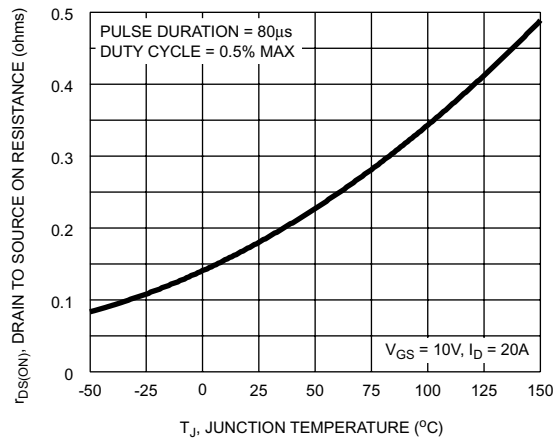


Figure 4. Drain To Source On Resistance vs Junction Temperature

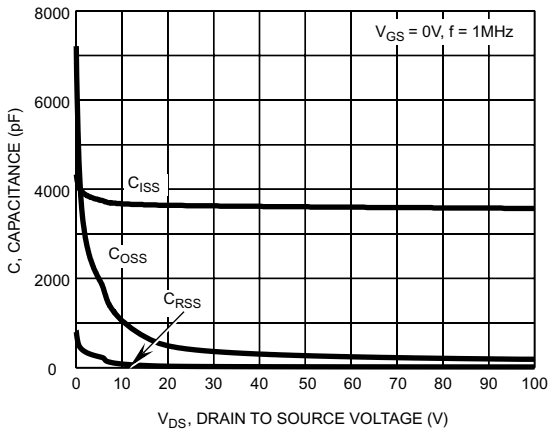


Figure 5. Capacitance vs Drain To Source Voltage

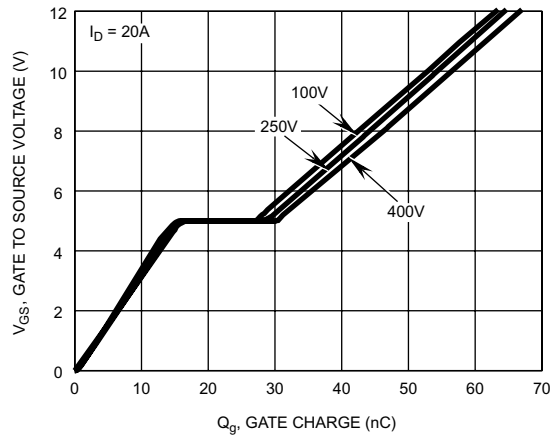


Figure 6. Gate Charge Waveforms For Constant Gate Current

Typical Characteristics (Continued)

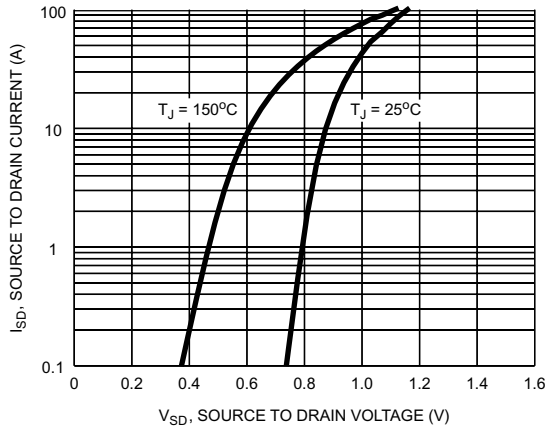


Figure 7. Body Diode Forward Voltage vs Body Diode Current

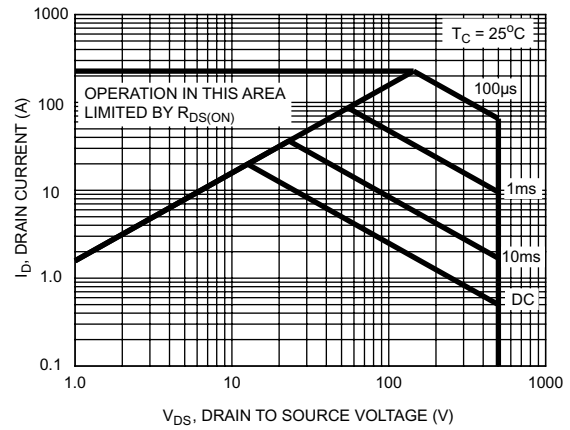


Figure 8. Maximum Safe Operating Area

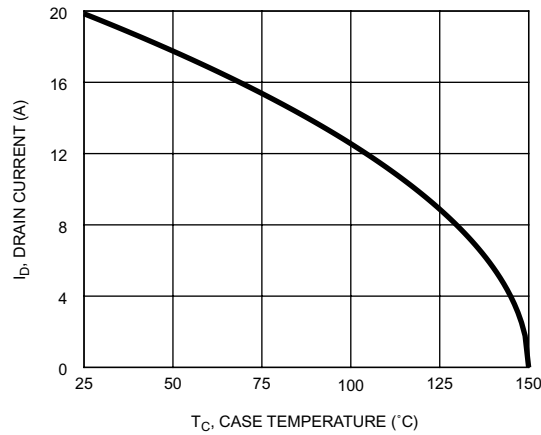


Figure 9. Maximum Drain Current vs Case Temperature

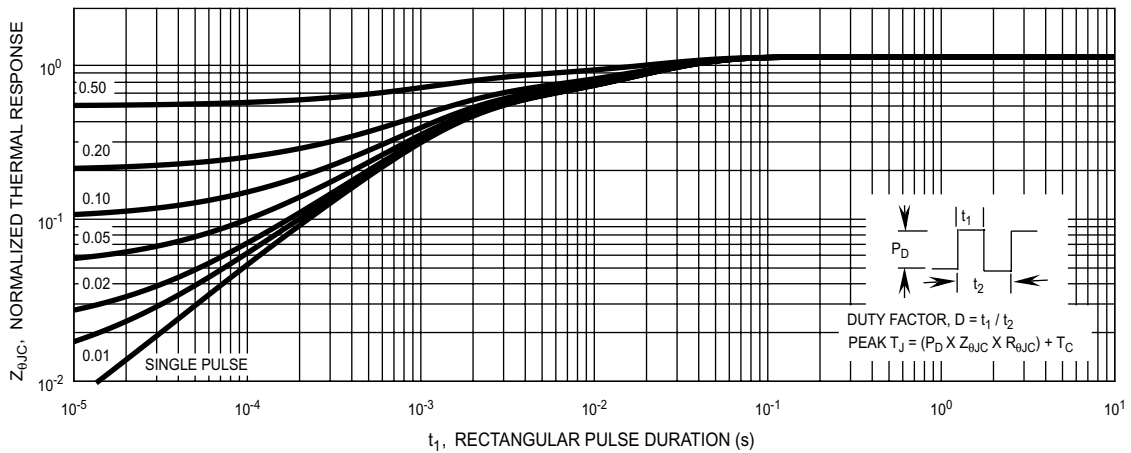


Figure 10. Normalized Transient Thermal Impedance, Junction to Case

Test Circuits and Waveforms

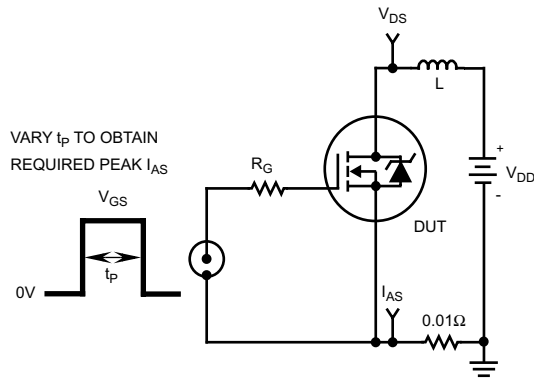


Figure 11. Unclamped Energy Test Circuit

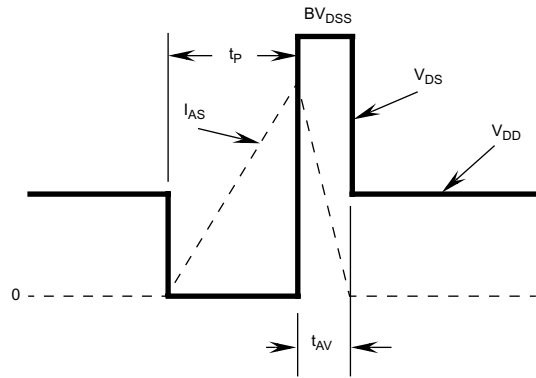


Figure 12. Unclamped Energy Waveforms

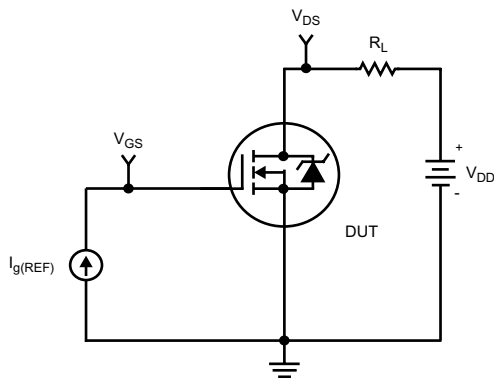


Figure 13. Gate Charge Test Circuit

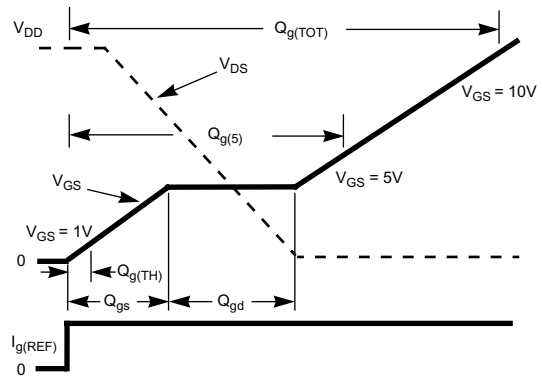


Figure 14. Gate Charge Waveforms

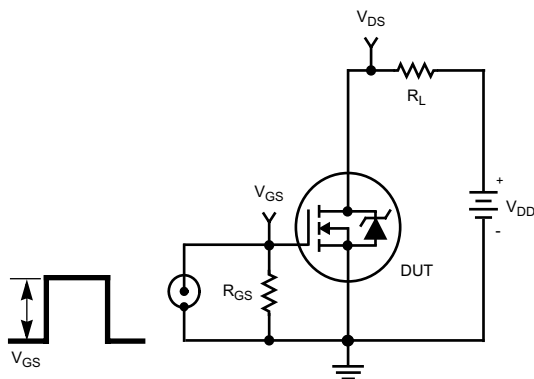


Figure 15. Switching Time Test Circuit

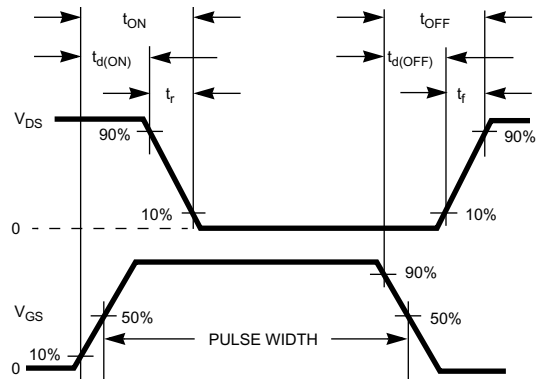


Figure 16. Switching Time Waveform

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